

MM54HC354/MM74HC354/ MM54HC356/MM74HC356 8-Channel TRI-STATE® Multiplexers with Latches

General Description

The MM54HC354/MM74HC354 and MM54HC356/ MM74HC356 utilize advanced silicon-gate CMOS technology. They exhibit the high noise immunity and low power dissipation of standard CMOS integrated circuits, along with the ability to drive 15 LS-TTL loads. Due to the large output drive capability and the TRI-STATE feature, these devices are ideally suited for interfacing with bus lines in a bus organized system.

These data selectors/multiplexers contain full on-chip binary decoding to select one of eight data sources. The data select address is stored in transparent latches that are enabled by a low level address on pin 11, SC. Data on the 8 input lines is stored in a parallel input/output register which in the MM54HC354/MM74HC354 is composed of 8 transparent latches enabled by a low level on pin 9, DC, and in the MM54HC356/MM74HC356 is composed of 8 edge-triggered flip-flops, clocked by a low to high transition on pin 9, CLK. Both true (Y) and complementary (W) TRI-STATE outputs are available on both devices.

The 54HC/74HC logic family is functionally as well as pinout compatible with the standard 54LS/74LS-TTL logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Transparent latches on data select inputs
- Choice of data registers:

Transparent ('354)

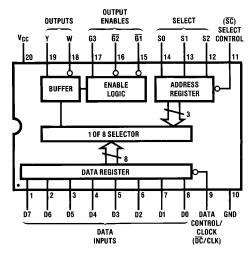
- Edge-triggered ('356)
- TRI-STATE complementary outputs with fanout of 15 LS-TTL loads
- Typical propagation delay:

Data to output ('354): 32 ns Clock to output ('346): 35 ns

- Wide power supply range: 2V-6V
- Low quiescent supply current: 80 µA maximum
- Low input current: 1 µA maximum

Connection Diagram

Dual-In-Line Package



TI /F/5208-1

Top View

Order Number MM54HC354/356 or MM74HC354/356

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Absolute Maximum Ratings (Notes 1 & 2) If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Power Dissipation (PD)

(Note 3) 600 mW S.O. Package only 500 mW

Lead Temp. (T_L)

(Soldering 10 seconds)

Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (TA)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times			
$(t_r, t_f) V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	v _{cc}	T _A =25°C		74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units
				Тур		Guaranteed Limits		
V _{IH}	Minimum High Level Input Voltage		2.0V 4.5V 6.0V		1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V V V
V _{IL}	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V		0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V V
V _{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \le 20 \mu A$	2.0V 4.5V 6.0V	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 6.0 \text{ mA}$ $ I_{OUT} \le 7.8 \text{ mA}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V
V _{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $ I_{OUT} \le 20 \mu A$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V V V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 6.0 \text{ mA}$ $ I_{OUT} \le 7.8 \text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V V
I _{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	μΑ
l _{OZ}	Maximum TRI-STATE Output Leakage Current	$V_{OUT} = V_{CC}$ or GND $\overline{G}1 = V_{IH}$	6.0V		±0.5	±5.0	± 10	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	μΑ

260°C

Note 1: Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V \pm 10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC}=5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

^{**}V_{IL} limits are currently tested at 20% of V_{CC}. The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $v_{CC}\!=\!5V,\, T_A\!=\!25^{\circ}C,\, t_r\!=\!t_f\!=\!6\,ns$

MM54HC354/MM74HC354

Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t _{PHL} , t _{PLH}	Maximum Propagation Delay D0-D7 to either Output	C _L =45 pF	32	46	ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay DC to either Output	C _L =45 pF	38	53	ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay S0-S2 to either Output	C _L =45 pF	40	56	ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay SC to either Output	C _L =45 pF	42	58	ns
t _{PZH} , t _{PZL}	Maximum Output Enable Time	$R_L = 1 k\Omega$ $C_L = 45 pF$	17	24	ns
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	$R_L = 1 k\Omega$ $C_L = 5 pF$	23	32	ns
ts	Minimum Setup Time D0-D7 to \overline{DC} , S0-S2 to \overline{SC}		3	10	ns
t _H	Minimum Hold Time D0-D7 to DC, S0-S2 to SC		0	5	ns
t _W	Minimum Pulse Width, SC or DC		10	15	ns

MM54HC356/MM74HC356

Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t _{PHL} , t _{PLH}	Maximum Propagation Delay CLK to either Output	C _L =45 pF	35	50	ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay S0-S2 to either Output	C _L =45 pF	40	56	ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay SC to either Output	C _L =45 pF	42	58	ns
t _{PZH} , t _{PZL}	Maximum Output Enable Time	$R_L = 1 \text{ k}\Omega$ $C_L = 45 \text{ pF}$	17	24	ns
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	$R_L = 1 k\Omega$ $C_L = 5 pF$	23	32	ns
t _S	Minimum Setup Time D0-D7 to CLK, S0-S2 to SC		3	10	ns
t _H	Minimum Hold Time D0-D7 to CLK, S0-S2 to SC		0	5	ns
t _W	Minimum Pulse Width, SC or CLK		10	15	ns

AC Electrical Characteristics $_{\rm MM54HC354/MM74HC354}$ (Continued) $_{\rm CC}=$ 2.0–6.0V, $_{\rm C_L}=$ 50 pF, $_{\rm t_f}=$ t_f=6 ns (unless otherwise specified)

Symbol	Parameter	Conditions	v _{cc}	T _A =	25°C	74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units
				Тур		Guaranteed Limits		
t _{PHL} , t _{PLH}	Maximum Propagation Delay D0-D7 to either Output	$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0V 2.0V	90 100	235 275	294 344	352 412	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	4.5V 4.5V	35 40	47 55	59 68	70 83	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	6.0V 6.0V	26 32	40 46	50 58	60 69	ns ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay DC to either Output	$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0V 2.0V	115 125	270 310	337 387	405 465	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	4.5V 4.5V	40 46	54 62	68 78	82 93	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	6.0V 6.0V	32 38	46 52	58 66	69 78	ns ns
$t_{\text{PHL}}, t_{\text{PLH}}$	Maximum Propagation Delay S0-S2 to either Output	$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0V 2.0V	120 130	285 325	356 406	427 488	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	4.5V 4.5V	42 50	57 65	71 81	86 97	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	6.0V 6.0V	34 40	48 55	60 69	72 82	ns ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay SC to either Output	$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0V 2.0V	120 110	300 340	375 425	450 510	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	4.5V 4.5V	45 52	60 68	75 85	90 102	ns ns
		C _L = 50 pF C _L = 150 pF	6.0V 6.0V	36 42	51 58	64 72	77 87	ns ns
t _{PZH} , t _{PZL}	Maximum Output Enable Time	$R_L = 1 \text{ k}\Omega$ $C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0V 2.0V	50 60	125 165	156 206	188 248	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	4.5V 4.5V	18 25	25 33	31 41	38 49	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	6.0V 6.0V	15 21	21 28	26 35	32 42	ns ns
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	$R_L = 1 \text{ k}\Omega$ $C_L = 50 \text{ pF}$	2.0V 4.5V 6.0V	68 24 20	165 33 28	206 41 35	248 49 42	ns ns ns
ts	Minimum Setup Time D0-D7 to DC, S0-S2 to SC		2.0V 4.5V 6.0V	6 3 3	50 10 10	60 13 13	75 15 15	ns ns ns
t _H	Minimum Hold Time D0-D7 to \overline{DC} , S0-S2 to \overline{SC}		2.0V 4.5V 6.0V	0 0 0	5 5 5	5 5 5	5 5 5	ns ns ns
t _W	Minimum Pulse Width SC or DC		2.0V 4.5V 6.0V	30 10 10	80 16 15	100 20 18	120 24 20	ns ns ns
t _{TLH} , t _{THL}	Maximum Output Rise and Fall Time	C _L =50 pF	2.0V 4.5V 6.0V	25 7 6	60 12 10	75 15 13	90 18 15	ns ns ns
C _{PD}	Power Dissipation Capacitance (Note 5)	(per package) Active TRI-STATE		150 50				pF pF
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF
C _{OUT}	Maximum Output Capacitance			15	20	20	20	pF

 $\textbf{Note 5:} C_{PD} \ \text{determines the no load dynamic power consumption,} \ P_D = C_{PD} \ V_{CC}^2 \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ \text{and the no load dynamic current consumption,} \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}, \ I_S = C_{PD} \ V_{CC} \ I_S = C_$

AC Electrical Characteristics $_{\rm MM54HC356/MM74HC356}$ (Continued) $_{\rm CC}=$ 2.0–6.0V, $_{\rm CL}=$ 50 pF, $_{\rm t_f}=$ t_f=6 ns (unless otherwise specified)

Symbol	Parameter	Parameter Conditions V _{CC} T _A =25°C		25°C	74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units	
				Тур		Guaranteed		
t _{PHL} , t _{PLH}	Maximum Propagation Delay CLK to either Output	$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0V 2.0V	100 110	225 295	318 369	338 442	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	4.5V 4.5V	36 42	51 59	63 73	76 90	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	6.0V 6.0V	28 34	43 50	53 63	64 75	ns ns
t_{PHL} , t_{PLH}	Maximum Propagation Delay S0-S2 to either Output	$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0V 2.0V	120 130	285 325	356 406	427 488	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	4.5V 4.5V	42 50	57 65	71 81	86 97	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	6.0V 6.0V	34 40	48 55	60 69	72 82	ns ns
t_{PHL} , t_{PLH}	Maximum Propagation Delay SC to either Output	$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0V 2.0V	120 110	300 340	375 425	450 510	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	4.5V 4.5V	45 52	60 68	75 85	90 102	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	6.0V 6.0V	36 42	51 58	64 72	77 87	ns ns
t _{PZH} , t _{PZL}	Maximum Output Enable Time	$R_L = 1 \text{ k}\Omega$ $C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0V 2.0V	50 60	125 165	156 206	188 248	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	4.5V 4.5V	18 25	25 33	31 41	38 49	ns ns
		$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	6.0V 6.0V	15 21	21 28	26 35	32 42	ns ns
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	$R_L = 1 \text{ k}\Omega$ $C_L = 50 \text{ pF}$	2.0V 4.5V 6.0V	68 24 20	165 33 28	206 41 35	248 49 42	ns ns ns
ts	Minimum Setup Time D0-D7 to CLK, S0-S2 to SC		2.0V 4.5V 6.0V	6 3 3	50 10 10	60 13 13	75 15 15	ns ns ns
t _H	Minimum Hold Time D0-D7 to CLK, S0-S2 to SC		2.0V 4.5V 6.0V	0 0 0	5 5 5	5 5 5	5 5 5	ns ns ns
t _W	Minimum Pulse Width SC to CLK		2.0V 4.5V 6.0V	30 10 10	80 16 15	100 20 18	120 24 20	ns ns ns
t _r , t _f	Maximum Clock Input Rise and Fall Time		2.0V 4.5V 6.0V		1000 500 400	1000 500 400	1000 500 400	ns ns ns
t _{TLH} , t _{THL}	Maximum Output Rise and Fall Time	C _L = 50 pF	2.0V 4.5V 6.0V	25 7 6	60 12 10	75 15 13	90 18 15	ns ns ns
C _{PD}	Power Dissipation Capacitance (Note 5)	(per package) Active TRI-STATE		150 50				pF pF
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF
C _{OUT}	Maximum Output Capacitance			15	20	20	20	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} \ V_{CC}^2 \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC}$

Function Table

	Inputs								
,	Select	†	Data Control 'HC354	Clock 'HC356		Output Out Enables		puts	
S1	S2	S0	DC	CLK	G ₁	G ₂	G3	w	Υ
Х	Х	Х	Х	Х	Н	Х	Х	Z	Z
X	X	Χ	Х	Х	X	Н	X	Z	Z
X	X	X	×	Х	X	X	L	Z	Z
L	L	L	L	1 ↑	L	L	Н	Ū0	D0
L	L	L	Н	H or L	L	L	Н	Ū0 _n	D0 _n
L	L	Н	L	1 ↑	L	L	Н	Ū1	D1
L	L	Н	Н	H or L	L	L	Н	⊡1 _n	D1 _n
L	Н	L	L	↑	L	L	Н	D2	D2
L	Н	L	Н	H or L	L	L	Н	$\overline{D}2_n$	D2 _n
L	Н	Н	L	1 ↑	L	L	Н	D 3	D3
L	Н	Н	Н	H or L	L	L	Н	Ū3 _n	D3 _n
Н	L	L	L	↑	L	L	Н	D̄4	D4
Н	L	L	Н	H or L	L	L	Н	Ū4 _n	D4 _n
Н	L	Н	L	1 ↑	L	L	Н	D̄5	D5
Н	L	Н	Н	H or L	L	L	Н	Ū5 _n	D5 _n
Н	Н	L	L	1 ↑	L	L	Н	D 6	D6
Н	Н	L	Н	H or L	L	L	Н	Ū6 _n	D6 _n
Н	Н	Н	L	1	L	L	Н	D7	D7
Н	Н	Н	Н	H or L	L	L	Н	Ū7 _n	D7 _n

H = high level (steady state)

L = low level (steady state)

X = irrelevant (any input, including transitions)

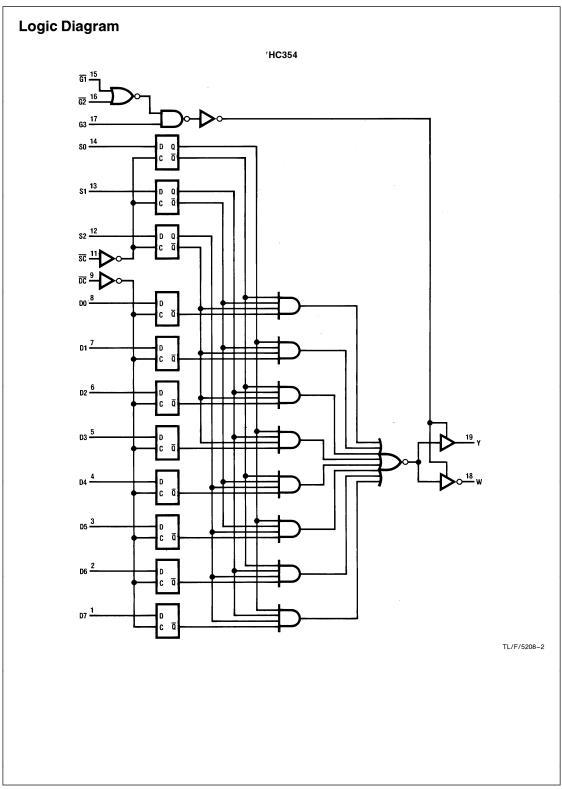
Z = high-impedance state (off state)

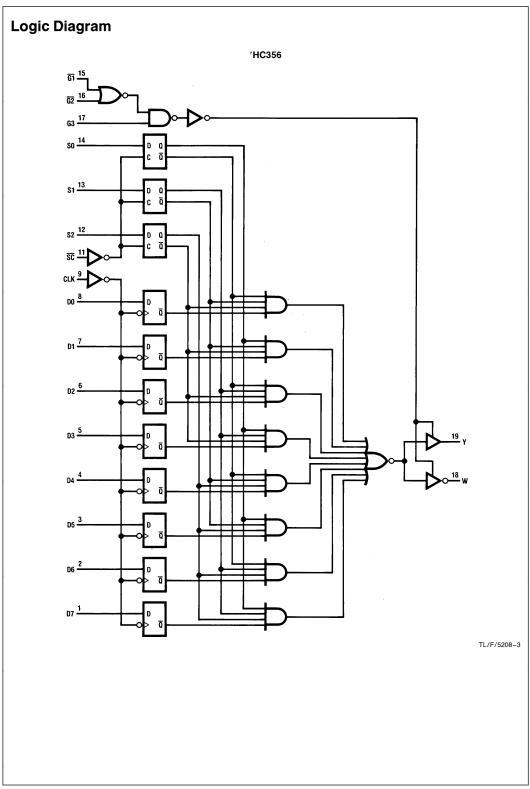
↑ = transition from low to high level

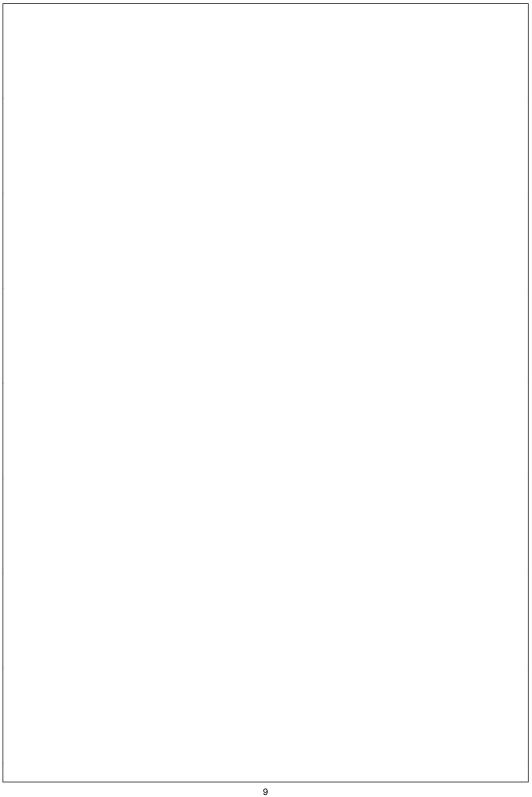
D0 ... D7 = the level steady-state inputs at inputs D0 through D7, respectively, at the time of the low-to-high clock transition in the case of 'HC356

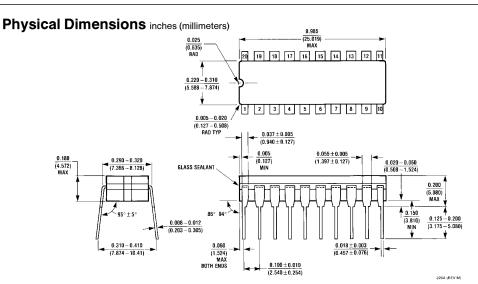
 $D_0 \dots D7_n =$ the level of steady state inputs at inputs D0 through D7, respectively, before the most recent low-to-high transition of data control or clock.

†This column shows the input address set-up with $\overline{\text{SC}}$ low.

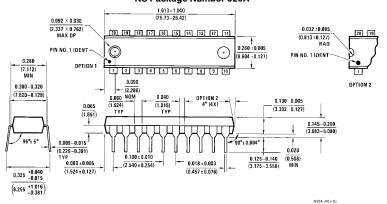








Ceramic Dual-In-Line Package (J) Order Number MM54HC354J, MM54HC356J, MM74HC354J or MM74HC356J NS Package Number J20A



Molded Dual-In-Line Package (N) Order Number MM74HC354N or MM74HC356N NS Package Number N20A

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